ABSTRACT OF THE DISCLOSURE

In a halftone phase shifting photomask 108, having a pattern of halftone phase shifting film 102 containing at least chromium and fluorine, the halftone phase shifting film is heat-treated at a temperature between 250 $^{\circ}$ C and 500 $^{\circ}$ C so that a change of the optical property of the film produced by the application of excimer laser for exposure to the film is decreased